



TSM8N70CI COG Information

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Part Number TSM8N70CI COG Manufacturer TSC America Inc.

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET, SINGLE, N-CHANNEL, PLANA

Package TO-220-3 Full Pack, Isolated Tab

For the pricing/inventory/lead time, please contact

us

For Reference Only

Website: https://www.heisener.com
E-mail: salesdept@heisener.com



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Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









TSM8N70CI C0G Specifications

Manufacturer Part Number TSM8N70CI COG Manufacturer TSC America Inc. Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack, Isolated Tab Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 700V Current - Continuous Drain (Id) @ 25°C 8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 32nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2006pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 40W (Tc) Rds On (Max) @ Id, Vgs 900 mOhm @ 4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package ITO-220 Package / Case TO-220-3 Full Pack, Isolated Tab		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack, Isolated Tab Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Tourent - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature A0W (Tc) Rds On (Max) @ Id, Vgs Power Dissipation (Max) Rds On (Max) @ Id, Vgs Through Hole Supplier Device Package Package / Case TO-220-3 Full Pack, Isolated Tab	Manufacturer Part Number	TSM8N70CI C0G
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Series - Channel FET Type N-Channel Technology MOSFET (Metal Oxide) Tourin to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 32nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2006pF @ 25V Vgs (Max) ±30V FET Feature - Continuous Max) 40W (Tc) Rds On (Max) @ Id, Vgs 900 mOhm @ 4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package 1TO-220 Package / Case		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)700VCurrent - Continuous Drain (Id) @ 25°C8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs32nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2006pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)40W (Tc)Rds On (Max) @ Id, Vgs900 mOhm @ 4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageITO-220Package / CaseTO-220-3 Full Pack, Isolated Tab	Package	TO-220-3 Full Pack, Isolated Tab
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Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs32nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2006pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)40W (Tc)Rds On (Max) @ Id, Vgs900 mOhm @ 4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageITO-220Package / CaseTO-220-3 Full Pack, Isolated Tab	Drain to Source Voltage (Vdss)	700V
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Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 40W (Tc) Rds On (Max) @ Id, Vgs 900 mOhm @ 4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package ITO-220 Package / Case TO-220-3 Full Pack, Isolated Tab	Gate Charge (Qg) (Max) @ Vgs	32nC @ 10V
FET Feature - Power Dissipation (Max) 40W (Tc) Rds On (Max) @ Id, Vgs 900 mOhm @ 4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package ITO-220 Package / Case TO-220-3 Full Pack, Isolated Tab	Input Capacitance (Ciss) (Max) @ Vds	2006pF @ 25V
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Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package ITO-220 Package / Case TO-220-3 Full Pack, Isolated Tab	Power Dissipation (Max)	40W (Tc)
Mounting Type Through Hole Supplier Device Package ITO-220 Package / Case TO-220-3 Full Pack, Isolated Tab	Rds On (Max) @ Id, Vgs	900 mOhm @ 4A, 10V
Supplier Device Package ITO-220 Package / Case TO-220-3 Full Pack, Isolated Tab	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3 Full Pack, Isolated Tab	Mounting Type	Through Hole
	Supplier Device Package	ITO-220
Report errors?	Package / Case	TO-220-3 Full Pack, Isolated Tab
		Report errors?

TSM8N70CI C0G Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

TSM8N70CI C0G Payment Methods





















TSM8N70CI C0G Shipping Methods













If you have any question about TSM8N70CI COG, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com